

AZ34063U

General Description

The AZ34063U is a monolithic switching regulator control circuit which contains the primary functions required for DC-DC converters. This device consists of internal temperature compensated reference, voltage comparator, controlled duty cycle oscillator with active current limit circuit, driver and high current output switch.

The AZ34063U is specifically designed as a general DC-DC converter to be used in Step-Down, Step-Up and Voltage-Inverting applications with a minimum number of external components.

The AZ34063U is available in 2 packages: SOIC-8 and DIP-8.

Features

- Operation from 3.0V to 36V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5A
- Output Voltage Adjustable
- Operation Frequency up to 180kHz
- Precision 2% Reference

Applications

- · Battery Chargers
- ADSL Modems
- Hubs
- Negative Voltage Power Supplies

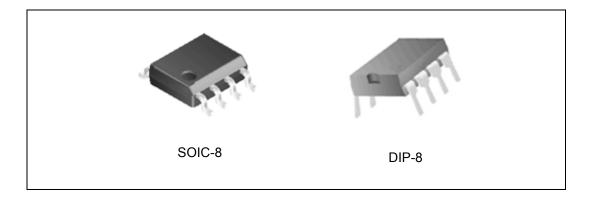


Figure 1. Package Types of AZ34063U



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Pin Configuration

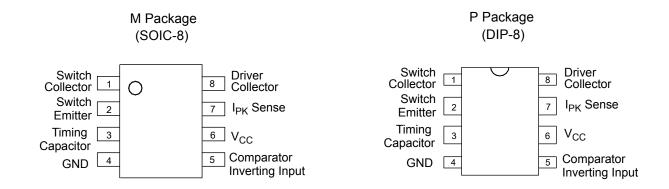


Figure 2. Pin Configuration of AZ34063U (Top View)

Functional Block Diagram

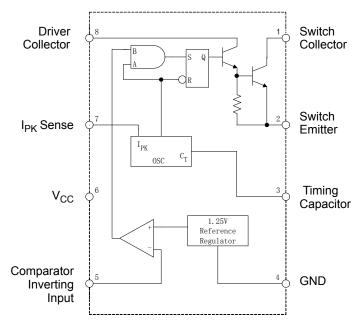


Figure 3. Functional Block Diagram of AZ34063U

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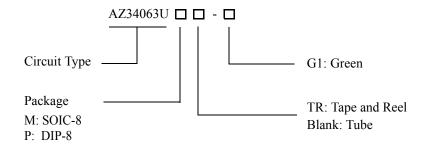


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Pin Description

Pin Number	Pin Name	Function
1	Switch Collector	Internal switch transistor collector
2	Switch Emitter	Internal switch transistor emitter
3	Timing Capacitor	Timing Capacitor to control the switching frequency
4	GND	Ground pin for all internal circuits
5	Comparator Inverting Input	Inverting input pin for internal comparator
6	V _{CC}	Voltage supply
7	I _{PK} Sense	Peak Current Sense Input by monitoring the voltage drop across an external current sense resistor to limit the peak cur- rent through the switch
8	Driver Collector	Voltage driver collector

Ordering Information



Package	Temperature Range	Part Number Marking ID		Packing Type	
SOIC-8	-40 to 85°C	AZ34063UM-G1	34063UM-G1	Tube	
		AZ34063UMTR-G1	34063UM-G1	Tape & Reel	
DIP-8	-40 to 85°C	AZ34063UP-G1	AZ34063UP-G1	Tube	

BCD Semiconductor's Pb-free products, as designated with "G1" suffix in the part number, are RoHS compliant and green.

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Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit	
Power Supply Voltage		V _{CC}	40	V
Comparator Input Voltage Range		V_{IR}	-0.3 to 40	V
Switch Collector Voltage		V _C (switch)	40	V
Switch Emitter Voltage (V _{PIN 1} =40V)		V _E (switch)	40	V
Switch Collector to Emitter Voltage	V _{CE} (switch)	40	V	
Driver Collector Voltage		V _C (driver)	40	V
Driver Collector Current (Note 2)		I _C (driver)	100	mA
Switch Current	I_{SW}	1.5	A	
Power Dissipation (T =250C)	DIP-8	P_{D}	1.25	W
Power Dissipation (T _A =25°C)	SOIC-8		780	mW
Thermal Resistance	DIP-8	θ_{JA}	100	0C/W
	SOIC-8		160	°C/W
Operating Junction Temperature		T_{J}	150	°C
Lead Temperature (Soldering, 10s)		$T_{ m LEAD}$	260	°C
Storage Temperature Range	T _{STG}	-65 to 150	°C	
ESD (Human body model)		2000	V	

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Note 2: Maximum package power dissipation limits must be observed.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	3	36	V
Ambient Temperature	T_{A}	-40	85	°C



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Electrical Characteristics

 $(V_{CC}=5.0V, T_A=-40 \text{ to } 85^{\circ}C, \text{ unless otherwise specified.})$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
OSCILLATOR				I.	<u>I</u>	
Frequency	$f_{ m OSC}$	V _{PIN5} =0V, C _T =1.0nF T _A =25°C	30	38	45	KHz
Charge Current	I_{CHG}	V _{CC} =5.0V to 36V, T _A =25°C	30	38	45	μΑ
Discharge Current	I _{DISCHG}	V _{CC} =5.0V to 36V, T _A =25°C	180	240	290	μΑ
Discharge to Charge Current Ratio	I _{DISCHG} /I _{CHG}	Pin 7 to V _{CC} , T _A =25°C	5.2	6.5	7.5	
Current Limit Sense Voltage	V _{IPK} (sense)	I _{CHG} =I _{DISCHG} , T _A =25°C 250		300	350	mV
OUTPUT SWITCH (Note 3)			I		
Saturation Voltage, Dalington Connection	V _{CE} (sat)	I _{SW} =1.0A, Pins 1, 8 connected, Common Emitter		1.0	1.3	V
Saturation Voltage (Note 4.)	V _{CE} (sat)	I_{SW} =1.0A, R_{PIN8} =82Ω to V_{CC} , Forced β=20, Common Emitter		0.45	0.7	V
DC Current Gain	h_{FE}	I _{SW} =1.0A, V _{CE} =5.0V, T _A =25°C	50	75		
Collector Off-State Current	I _C (off)	V _{CE} =36V		0.01	100	μΑ
COMPARATOR		1		I.	<u>I</u>	
	V_{TH}	T _A =25°C	1.225	1.250	1.275	
Threshold Voltage		T _A =-40 to 85°C	1.21	1.250	1.29	V
Threshold Voltage Line Regulation REGLINE		V _{CC} =3.0V to 36V		1.4	5	mV
Input Bias Current	I _{IB}	$V_{IN}=0V$		-20	-400	nA
TOTAL DEVICE		<u> </u>		ı		
Supply Current	I _{CC}	V_{CC} =5.0V to 36V, C_T =1.0nF, V_{PIN7} = V_{CC} , V_{PIN5} > V_{TH} , V_{PIN2} =GND, other pins open			4	mA

Note 3: Low duty cycle pulse technique are used during test to maintain junction temperature as close to ambient temperature as possible.

Note 4: If the output switch is driven into hard saturation (non-Darlington configuration) at low switch currents ($\leq 30 \text{mA}$) and high driver currents ($\geq 30 \text{mA}$), it may take up to $2.0 \mu \text{s}$ for it to come out of saturation. This condition will shorten the off time at frequencies 30KHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

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Electrical Characteristics (Continued)

Forced β of output switch: $\frac{I_C \ output}{I_C driver \ \hbox{--} \ 7.0 mA^*} {\ge 10}$

Typical Performance Characteristics

(V_{CC} =5.0V, T_A =25°C, unless otherwise specified.)

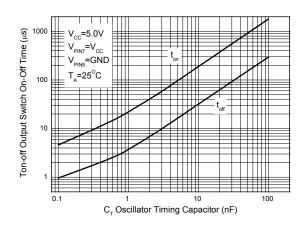


Figure 4. Output Switch On-Off Time vs. Oscillator Timing Capacitor

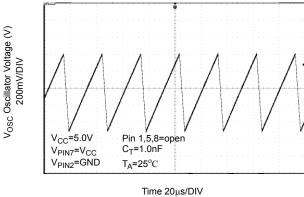


Figure 5. Timing Capacitor Waveform

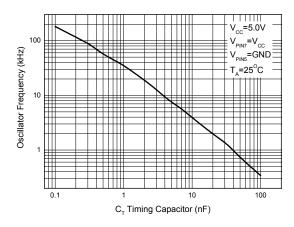


Figure 6. Oscillator Frequency vs.Timing Capacitor

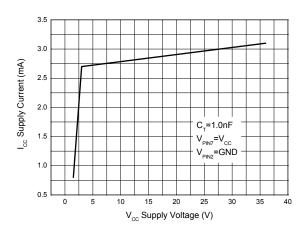


Figure 7. Standard Supply Current vs. Supply Voltage

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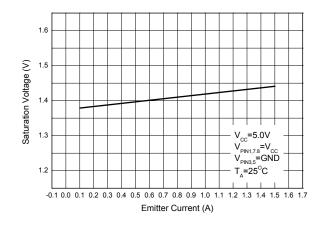
^{*} The 100Ω resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.



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Typical Performance Characteristics (Continued)

(V_{CC}=5.0V, T_A=25°C, unless otherwise specified.)



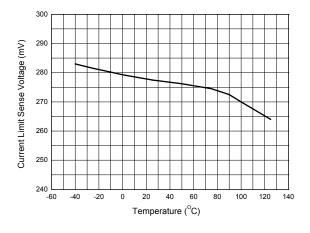
1.4
1.2
1.0
Darlington Connection

0.6
Forced β=20
V_{PIN2.3.5}=GND
V_{PIN2.3.5}=GND
T_A=25°C

0.0
0.0
0.2
0.4
0.6
0.8
1.0
1.2
1.4
1.6
Collector Current (A)

Figure 8. Emitter Follower Configuration Output
Saturation Voltage vs. Emitter current

Figure 9. Common Emitter Configuration Output Switch Saturation Voltage vs. Collector Current



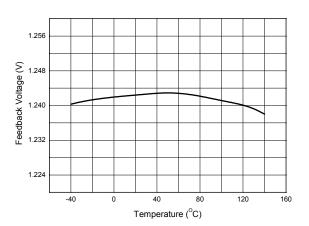


Figure 10. Current Limit Sense Voltage vs. Temperature

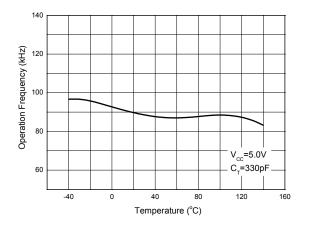
Figure 11. Feedback Voltage vs. Temperature



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Typical Performance Characteristics (Continued)

(V_{CC} =5.0V, T_A =25°C, unless otherwise specified.)



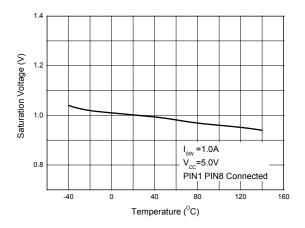


Figure 12. Operation Frequency vs. Temperature

Figure 13. Saturation Voltage vs. Temperature



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Typical Applications

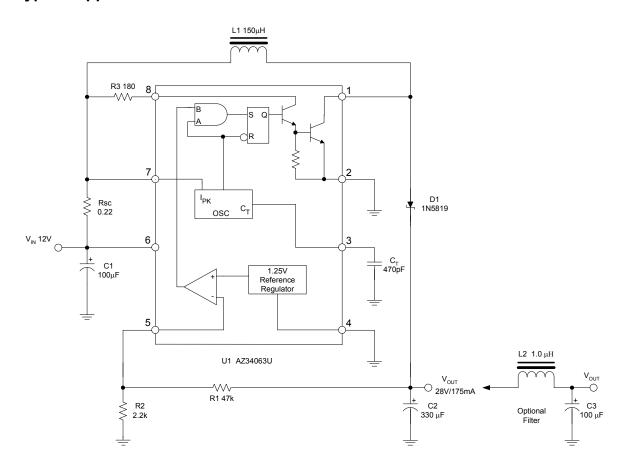


Figure 14. Step-Up Converter (Note 5)

Note 5: This is a typical step-up converter configuration. In the steady state, if the resistor divider voltage at pin 5 is greater than the voltage in the non-inverting input, which is 1.25V determined by the internal reference, the output of the comparator will go low. At the next swithching period, the output switch will not conduct and the output voltage will eventually drop below its nominal voltage until the divider voltage at pin 5 is lower than 1.25V. Then the output of the comparator will go high, the output switch will be allowed to conduct. Since $V_{PIN5} = V_{OUT}^* \times R2/(R1+R2) = 1.25(V)$, the output voltage can be decided by $V_{OUT} = 1.25 \times (R1+R2)/R2$ (V).

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Typical Applications (Continued)

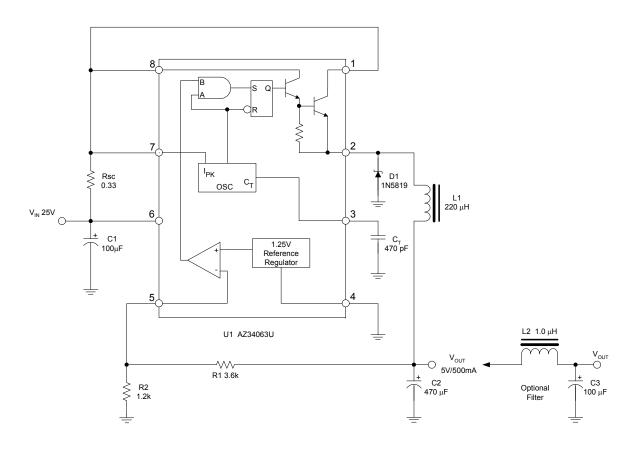


Figure 15. Step-Down converter (Note 6)

Note 6: This is a typical step-down converter configuration. The working process in the steady state is similar to step-up converter, $V_{PIN5}=V_{OUT}*R2/(R1+R2)=1.25$ (V), the output voltage can be decided by $V_{OUT}=1.25*(R1+R2)/R2$ (V).

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Typical Applications (Continued)

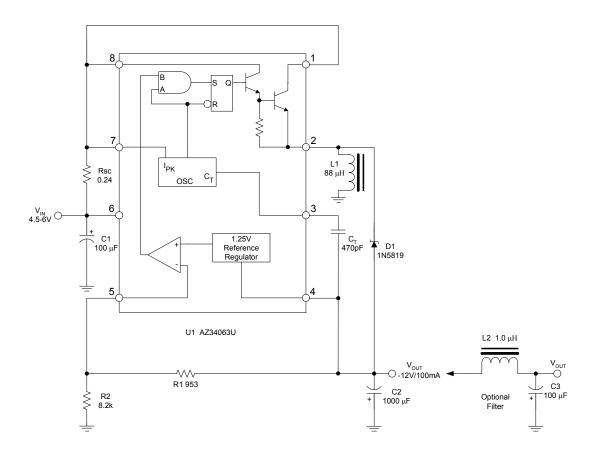


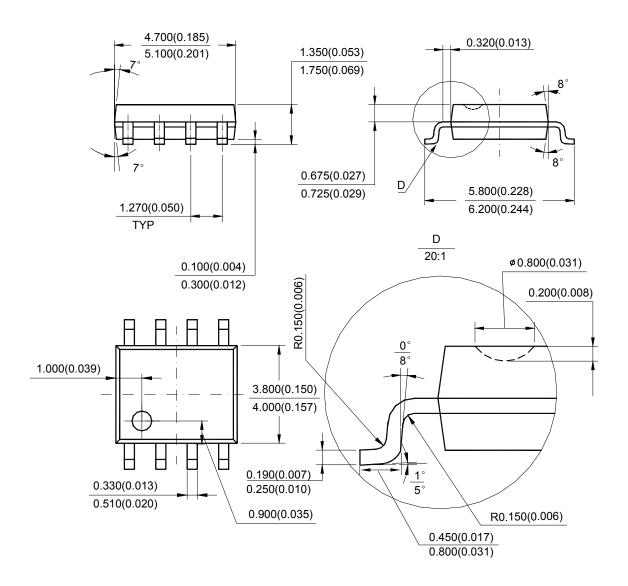
Figure 16. Voltage Inverting Converter (Note 7)

Note 7: This is a typical inverting converter configuration. The working process in the steady state is similar to step-up converter, the difference in this situation is that the voltage at the non-inverting pin of the comparator is equal to 1.25V+V $_{OUT}$, then V $_{PIN5}$ =V $_{OUT}$ *R2/(R1+R2)=1.25V+V $_{OUT}$, so the output voltage can be decided by V $_{OUT}$ =-1.25*(R1+R2)/R1 (V).

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Mechanical Dimensions

SOIC-8 Unit: mm(inch)



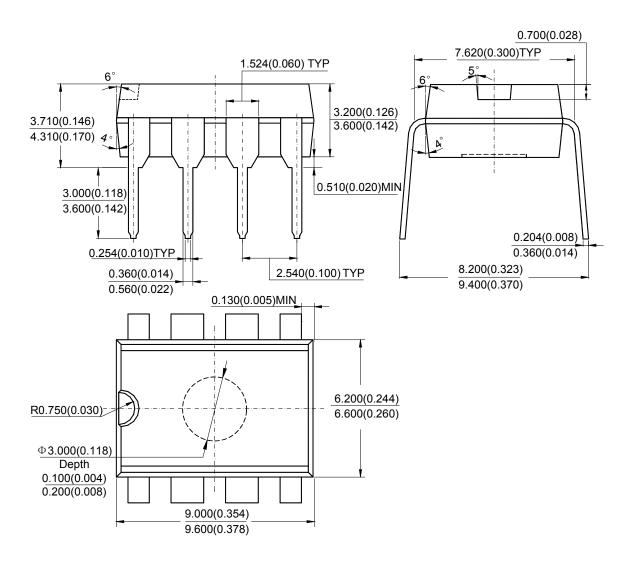
Note: Eject hole, oriented hole and mold mark is optional.



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Mechanical Dimensions (continued)

DIP-8 Unit: mm(inch)



Note: Eject hole, oriented hole and mold mark is optional.





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